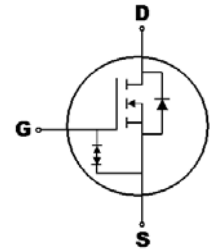


N-Channel Enhancement Mode MOSFET

Feature

- 60V/0.5A, $R_{DS(ON)} = 2000\text{m}\Omega$ (MAX) @ $V_{GS} = 10\text{V}$, $I_D = 0.5\text{A}$
 $R_{DS(ON)} = 2500\text{m}\Omega$ (MAX) @ $V_{GS} = 4.5\text{V}$, $I_D = 0.2\text{A}$
 $R_{DS(ON)} = 4500\text{m}\Omega$ (MAX) @ $V_{GS} = 2.5\text{V}$, $I_D = 0.1\text{A}$
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- ESD Protection : $\text{HBM} \geq 1.5\text{KV}$
- SOT-23 for Surface Mount Package.



Applications

- Power Management in Desktop Computer or DC/DC Converters .

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	0.5	A

Electrical Characteristics

$T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0\text{V}$, $I_D=10\mu\text{A}$	60	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	10	μA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-20\text{V}$, $V_{DS}=0\text{V}$	-	-	-10	μA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D=250\mu\text{A}$	0.85	1.2	2.5	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 0.5\text{A}$	-	1200	2000	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}$, $I_D = 0.2\text{A}$	-	1400	2500	$\text{m}\Omega$
		$V_{GS} = 2.5\text{V}$, $I_D = 0.1\text{A}$	-	-	4500	$\text{m}\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS} = 0\text{V}$, $I_S = 0.2\text{A}$			1.5	V

Typical Characteristics

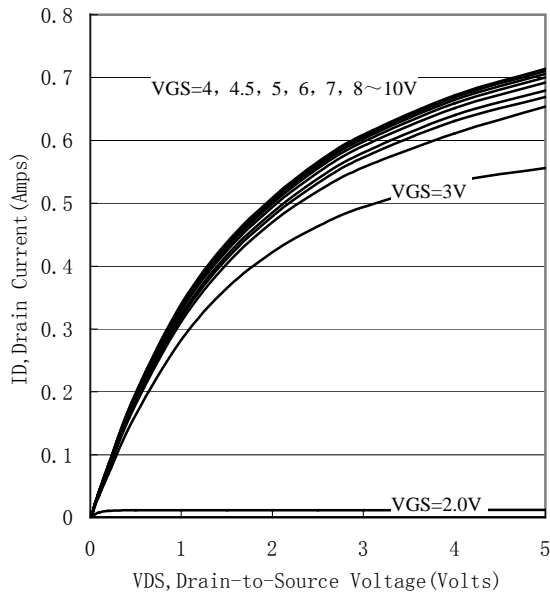


Figure 1. Output Characteristics

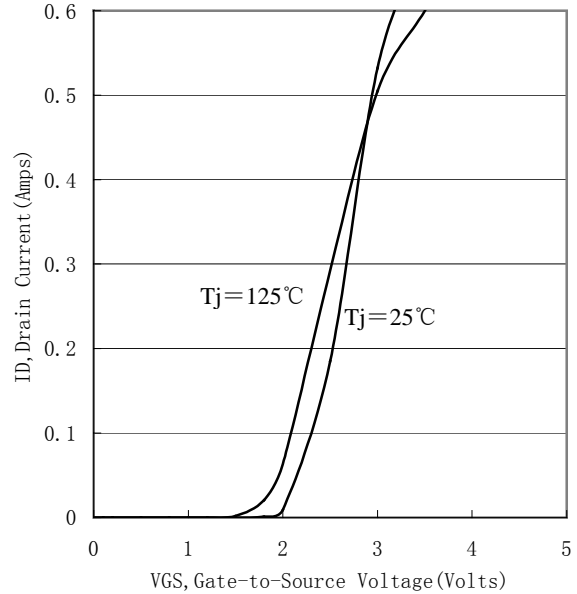


Figure 2. Transfer Characteristics

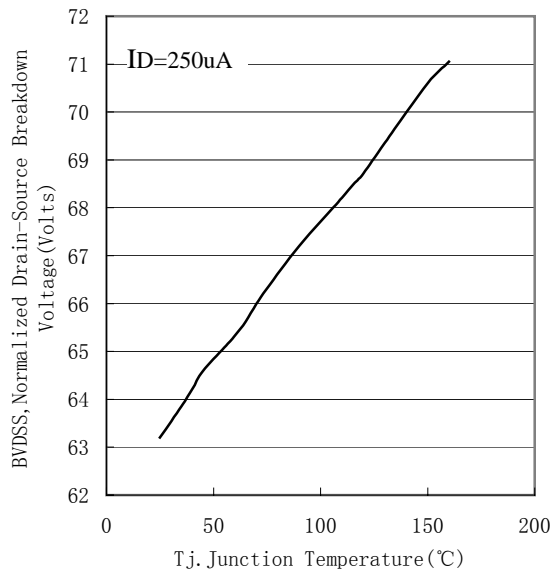


Figure 3. Breakdown Voltage Variation with Temperature

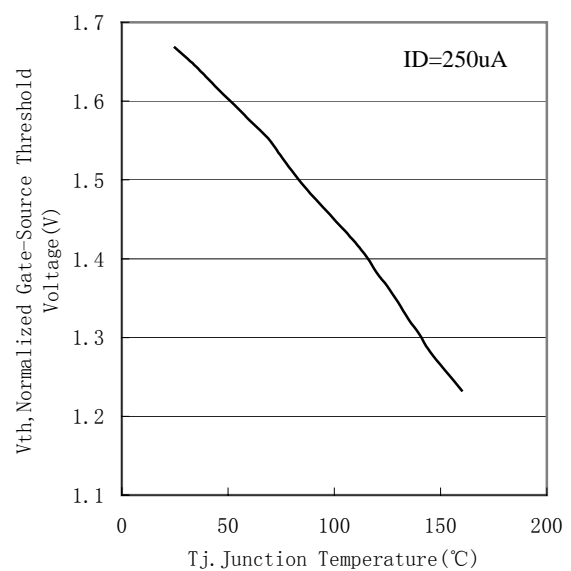


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

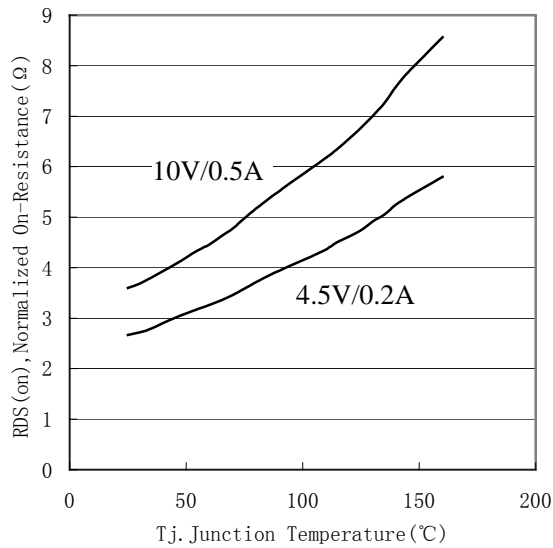


Figure 5. On-Resistance Variation with Temperature

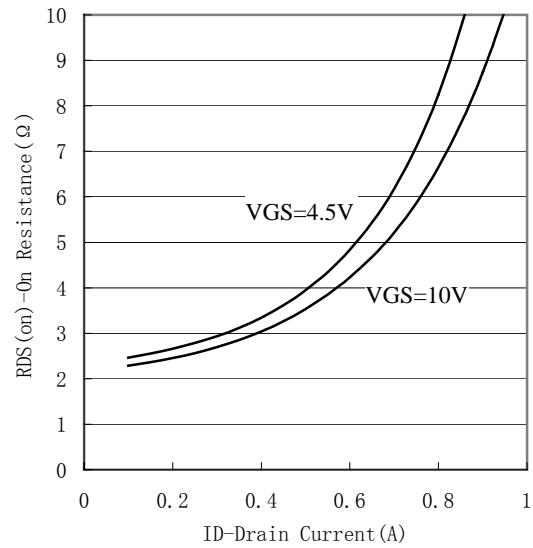


Figure 6. On-Resistance vs. Drain Current

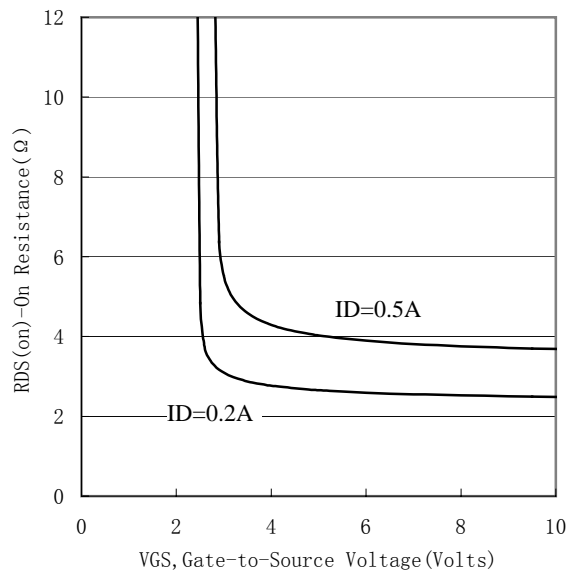


Figure 7. On-Resistance vs. Gate-to-Source Voltage

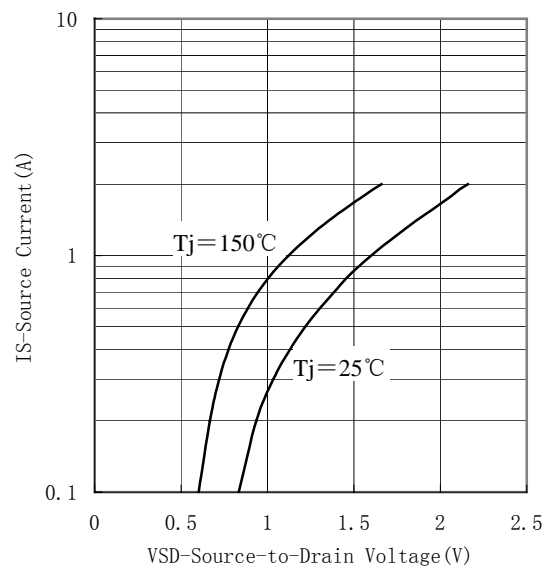


Figure 8. Source-Drain Diode Forward Voltage

单击下面可查看定价，库存，交付和生命周期等信息

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